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Publisher Correction: Interlayer excitons in a bulk van der Waals semiconductor

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In the PDF version of this article, Equation 1 is missing an epsilon at the beginning. The correct version of Equation 1 is below. The HTML version of the paper was correct from the time of publication.

$$\epsilon(E) = (n_b + ik_b)^2 + \frac{A}{E_0^2 - E^2 - i\gamma E}$$

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